Session Title: 53. Oxide TFTs: High Performance

Date: Aug. 31, 2017 (Thursday)

Time: 09:00-10:30

Room E (Room 104-105)

Session Chairs Prof. Yukiharu Uraoka (NAIST, Japan)

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**[E53-1]** 09:00-09:25

[Invited] Quantitative Analysis of Coplanar a-IGZO TFTs for High Reliability Device

Jiyong Noh, Ju-heyuck Baeck, Jong Uk Bae, Kwon-Shik Park, SooYong Yoon, and In Byeong Kang (LG Display Co., Ltd., Korea)

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**[E53-2]** 09:25-09:50

[Invited] Stability Investigation on Amorphous InSnZnO Thin Film Transistors with a Top Nitrogen Doped Active Layer

Gongtan Li, Chuan Liu, and Bo-Ru Yang (Sun Yat-Sen Univ., China)

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**[E53-3]** 09:50-10:15

[Invited] Short Channel Oxide TFTs for Digital Holography

Chi-Sun Hwang, Jong-Heon Yang, JiHun Choi, Jae-Eun Pi, Kyunghee Choi, Chi-Young Hwang, Yong-Hae Kim, Gi Heon Kim (ETRI, Korea), Sang-Hee Ko Park (KAIST, Korea), and Jinwoong Kim (ETRI, Korea)

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**[E53-4]** 10:15-10:30

Development of a 55-in 4K UHD OLED TV with High Reliability and Short Channel IGZO TFTs

Mijeong Park, Hyunmin Cho, Woocheol Jeong, Jaeyong Park, and Jongwoo Kim (LG Display Co., Ltd., Korea)